

1. (Thrice Amended) A method for fabricating a metallization structure, comprising:

ion metal plasma depositing a wetting layer within a cavity of a dielectric layer;

applying a sufficient bias power to splash deposited metal at the bottom of the cavity to sidewalls of the cavity, wherein said applying occurs during said ion metal plasma depositing the wetting layer; and

sputter depositing, within a single chamber, substantially an entirety of a bulk metal layer upon the wetting layer.

#### REMARKS

Claim 1 has been amended. Claims 24-29 have been withdrawn due to a restriction cited in the Office Action. Thus, claims 1-18, 22, 23, and 30 are currently pending in the case. Further examination and reconsideration of the presently claimed application is respectfully requested.

#### Allowable Claims:

Allowance of claims 12-18, 22, and 23 is gratefully acknowledged.

#### Election/Restriction of Claims:

Claims 24-29 were withdrawn from consideration in the Office Action as being directed to a non-elected invention. However, Applicants reserve the right to file a divisional application at a later date capturing the subject matter recited in non-elected claims 24-29.

#### Section 112, 1st Paragraph, Rejection:

Claims 1-11 were rejected under 35 U.S.C. § 112, first paragraph for the specification not providing enablement of the claim limitations. To expedite prosecution, claim 1 has been amended. This modification is believed to clarify the claim language in a manner that addresses the concerns expressed in the Office Action. This modification is for clarification purposes only